

DESCRIPTION

Mitsubishi 2SC2603 is a silicon NPN epitaxial type transistor designed for low frequency voltage amplify application. Small package for easy mounting.

FEATURE

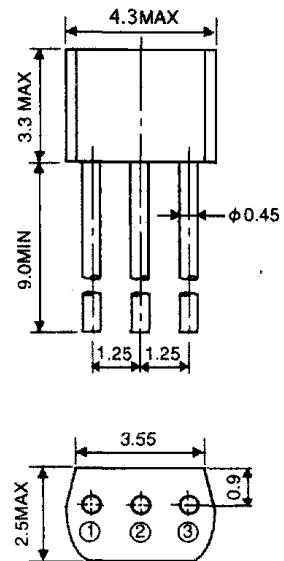
- Excellent lineary of DC forward current gain
- Low collector saturation voltage $V_{CE(sat)}=0.3V_{max}$ (@ $I_C=100mA, I_B=10mA$)
- Small package

APPLICATION

For small machine low frequency voltage amplify application.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ① : EMITTER EIAJ : —
- ② : COLLECTOR JEDEC : —
- ③ : BASE

Note)
The dimension without tolerance represent central value.

MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V _{CB0}	Collector to Base voltage	50	V
V _{EB0}	Emitter to Base voltage	6	V
V _{CE0}	Collector to Emitter voltage	50	V
I _C	Collector current	200	mA
P _C	Collector dissipation(Ta=25°C)	300	mW
T _J	Junction temperature	+125	°C
T _{stg}	Storage temperature	-55 to +125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{(BR)CEO}	C to E break down voltage	I _C =100 μA, R _{BE} =∞	50			V
I _{CB0}	Collector cut off current	V _{CB} =50V, I _E =0			0.1	μA
I _{EB0}	Emitter cut off current	V _{EB} =6V, I _C =0			0.1	μA
h _{FE} *	DC forward current gain	V _{CE} =6V, I _C =1mA	90		800	—
h _{FE}	DC forward current gain	V _{CE} =6V, I _C =0.1mA	50			—
V _{CE(sat)}	C to E saturation voltage	I _C =100mA, I _B =10mA			0.3	V
f _T	Gain band width product	V _{CE} =6V, I _E =-10mA		200		MHz
C _{ob}	Collector output capacitance	V _{CB} =6V, I _E =0, f=1MHz		2.5		pF
NF	Noise figure	V _{CE} =6V, I _E =-0.1mA, f=1kHz, R _G =2kΩ			15	dB

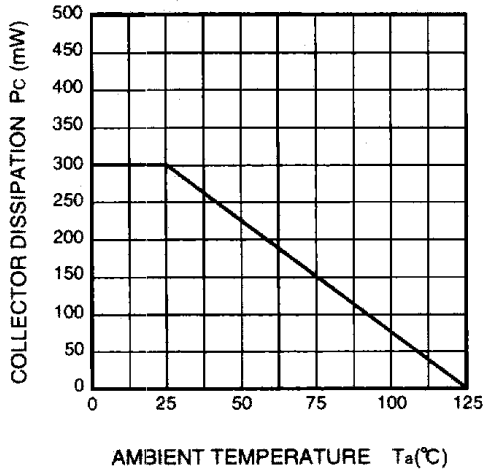
* : It shows h_{FE} classification in right table.

Item	D	E	F	G
h _{FE}	90 to 180	150 to 300	250 to 500	400 to 800

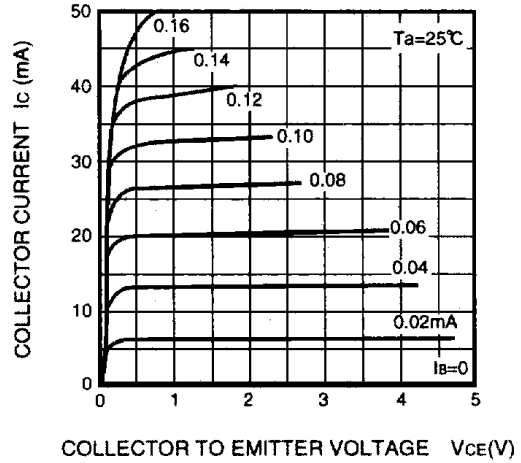
FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON NPN EPITAXIAL TYPE

TYPICAL CHARACTERISTICS

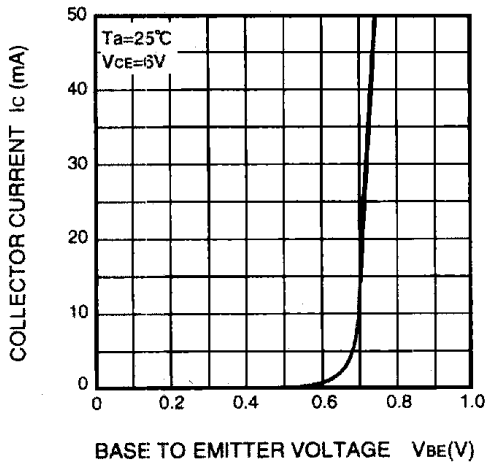
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



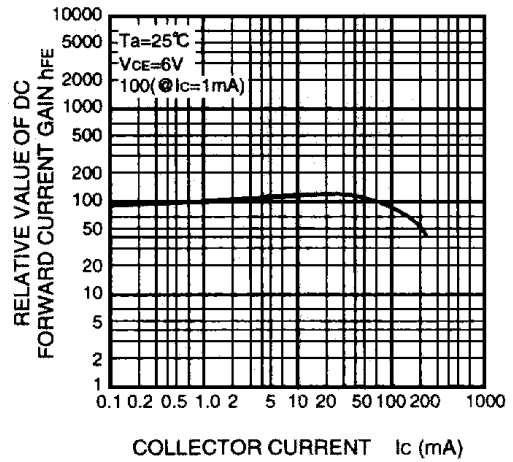
COMMON EMITTER OUTPUT



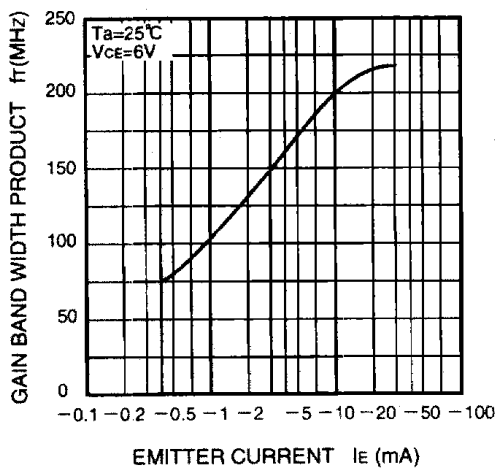
COMMON EMITTER TRANSFER



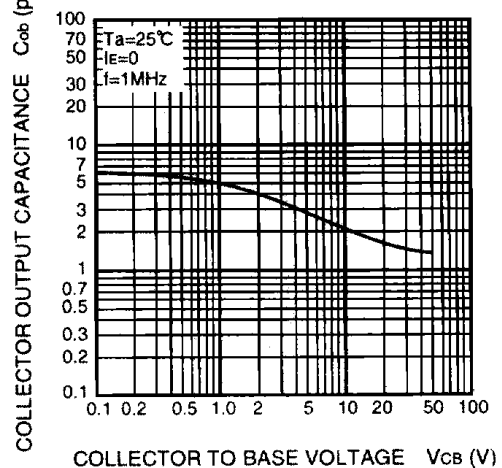
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



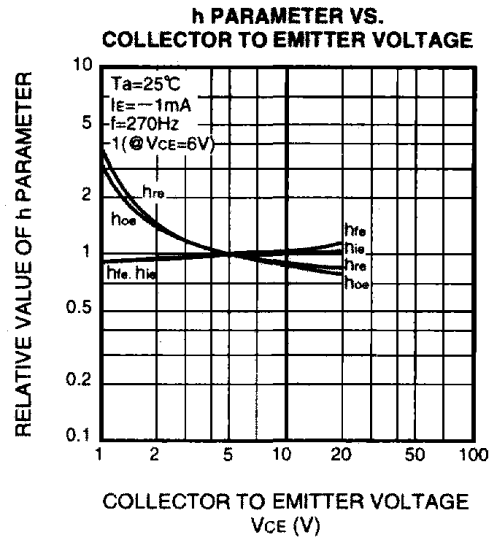
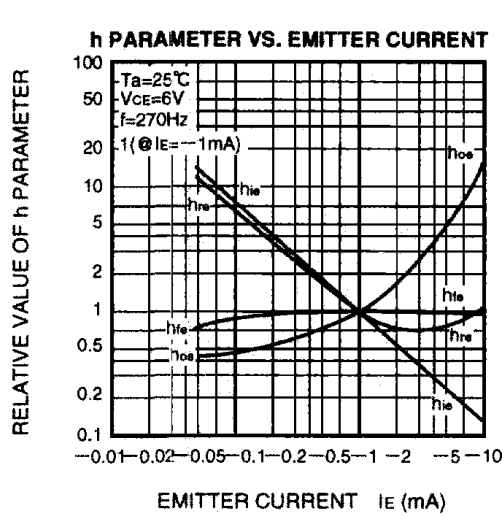
GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON NPN EPITAXIAL TYPE



COMMON EMITTER h PARAMETER (TYPICAL VALUE)

Symbol	Parameter	Test conditions	Limits	Unit
h_{ie}	Closed loop small signal input impedance	$T_a=25^\circ\text{C}$ $V_{CE}=6\text{V}$ $I_E=-1\text{mA}$ $f=270\text{Hz}$	8.5	$\text{k}\Omega$
h_{re}	Open loop small signal reverse voltage amplification factor		0.1	$\times 10^{-3}$
h_{fe}	Closed loop small signal forward current amplification factor		300	—
h_{oe}	Open loop small signal output admittance		5.5	μS